



5LN01C

ON Semiconductor®

SPICE PARAMETER

Nch MOS FET

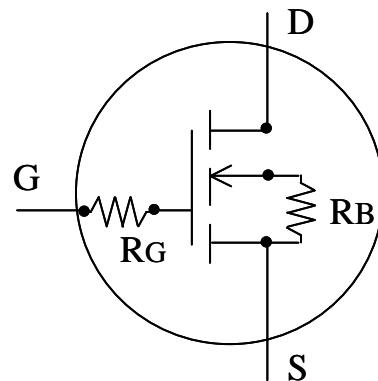
model : BSIM3V3.2

Parameter	Value	Parameter	Value	Parameter	Value
LEVEL	8				
VERSION	3.2	TNOM	27	TOX	3.0E-08
VTH0	0.78	K1	1.96	K2	-0.04
NLX	1.7E-07	DVT0	3.12	DVT1	0.58
DVT2	-0.01	U0	600	UA	0
UB	1.0E-21	VSAT	6.0E+06	A0	0
AGS	-0.1	A1	0	A2	1
RDSW	4.2E+03	PRWG	-3.16E-04	WR	0.82
WINT	0	LINT	1.5E-07	VOFF	-0.15
NFACTOR	0.48	CIT	0	CDSC	2.4E-04
CDSCD	0	ETA0	0	DSUB	0.96
PCLM	4.3	PDIBLC1	0	PDIBLC2	1.0E-05
DROUT	0.96	PSCBE1	3.8E+09	PSCBE2	1.0E-05
PVAG	0.01	DELTA	1.0E-03	NGATE	1.0E+19
MOBMOD	1	NQSMOD	0	NOIMOD	1
CAPMOD	3	XPART	0.5	CGSO	6.0E-11
CGDO	1.0E-10	CGBO	0	CGSL	0
CGDL	2.0E-09	CKAPPA	1.2	CF	0
CLC	3.0E-09	CLE	0.8	DWC	0
DLC	-6.0E-07	NOFF	3.66	VOFFCV	-0.4
ACDE	1.0	MOIN	15	CJ	1.5E-03
MJ	0.26	PB	0.5	JS	2.5E-06
NJ	1.01	XTI	3.0	IJTH	0
KT1	-0.4	UTE	-0.2	PRT	1.0E+04
AT	3.3E+04				

Temp = 27 deg
L = 1.0E-6 m
W = 3988E-6 m
AD = 3988E-12 m2
RG = 4657 ohm
RB = 0.55 ohm

Date : 2007/02/05

*Information herein is for example only ;
It is not guaranteed for volume production.



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